



100V PNP ULTRA-LOW VCE(sat) TRANSISTOR IN PowerDI3333-8

Features

- BVcEo > -100V
- BV_{EBO} > -8V
- Continuous Current Ic to -2.5A
- Peak Pulse Current Icm to -8A
- Ultra-Low Saturation Voltage V_{CE(sat)} < -85mV @ -1A
- High Current R_{CE(sat)} = 60mΩ Typical
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Rated to +175°C Ideal for High-Temperature Environments
- Complementary NPN Type: <u>DXTN78100CFGQ</u>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTP78100CFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin.
 Solderable per MIL-STD-202. Method 208 @3.
- Weight: 0.03 grams (Approximate)

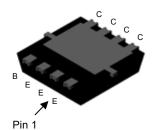
Applications

- MOSFET & IGBT gate drivers
- Load switches
- Low-voltage regulation
- DC to DC converters
- Motors, solenoids, relays and actuator drivers control

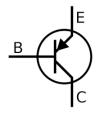
PowerDI3333-8/SWP (Type UX)



Top View



Bottom View



Device Symbol

Ordering Information (Note 4)

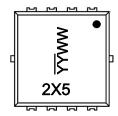
Orderable Part Number	Package	Marking Reel Size (inches)	c) Tone Width (mm)	Packing		
Orderable Part Number	Package	Warking	Reel Size (Iliches)	rape width (IIIII)	Qty.	Carrier
DXTP78100CFGQ-7	PowerDI3333-8/SWP (Type UX)	2X5	7	12	2,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8/SWP (Type UX)



2X5 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 25 = 2025)
 WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated in the United States and other countries.



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	-110	V
Collector-Emitter Voltage	Vceo	-100	V
Emitter-Base Voltage	VEBO	-8	V
Continuous Collector Current (Note 5)	Ic	-1.5	Α
Continuous Collector Current (Note 7)	Ic	-2.5	Α
Peak Pulse Current	Ісм	-8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		900	mW
Power Dissipation	(Note 6)	PD	1.6	W
	(Note 7)		2.4	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	92	°C/W
	(Note 7)		62.5	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	8	°C/W	
Thermal Resistance, Junction to Lead (Note 8)	Rejl	6.5	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Electrostatic Discharge - Charged Device Model	ESD CDM	1,000	V	IV

Notes:

- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Thermal resistance from junction to solder-point (at the collector tab).
 9. Refer to JEDEC specifications JESD22-A114, JESD22-A115 and JESD22-C101.



Thermal Characteristics and Derating Information

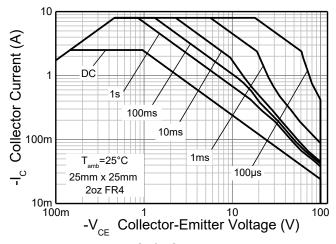


Fig 1. Safe Operating Area

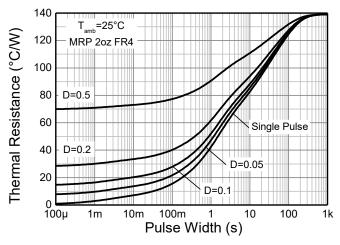


Fig 2. Transient Thermal Impedance

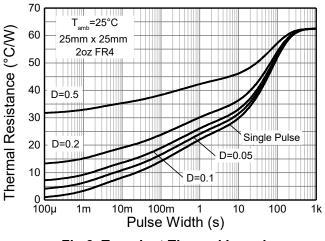


Fig 3. Transient Thermal Impedance

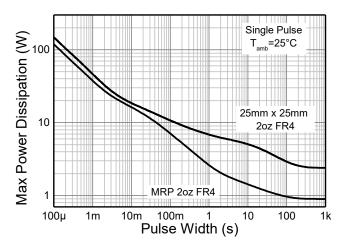


Fig 4. Pulse Power Dissipation

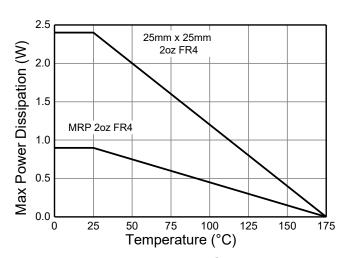


Fig 5. Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	ВУсво	-110	_	_	V	Ic = -100μA	
Collector-Emitter Breakdown Voltage (Note 10)	BVceo	-100	_	_	V	I _C = -10mA	
Emitter-Collector Breakdown Voltage	BVECO	-5	_	_	V	I _E = -100μA	
Emitter-Base Breakdown Voltage	BV _{EBO}	-8	_	_	V	I _E = -100μA	
Collector Cutoff Current	Ісво	_	_	-100	nA	V _{CB} = -110V	
Collector Cutoff Current		_	_	1	μΑ	V _{CB} = -110V, T _A = +125°C	
Collector Cutoff Current	ICES	_	_	-300	nA	V _{CE} = -80V	
Emitter Cutoff Current	I _{EBO}	_	_	-50	nA	V _{EB} = -7V	
		_	-90	_	mV	Ic = -100mA, I _B = -1mA	
		_	-110	-160	mV	I _C = -1A, I _B = -50mA	
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	-70	-85	mV	I _C = -1A, I _B = -100mA	
		_	-90	-125	mV	I _C = -1.5A, I _B = -150mA	
		_	-165	-300	mV	I _C = -2.5A, I _B = -250mA	
Dana Fraittan Caturation Valtana (Nota 10)	V _{BE} (sat)	_	-860	-950	mV	Ic = -1.5A, I _B = -150mA	
Base-Emitter Saturation Voltage (Note 10)		_	-930	-1,050	mV	I _C = -2.5A, I _B = -250mA	
Dana Fraittan Turra On Valtana (Nata 40)	VBE(on)	_	-750	-850	mV	Ic = -1.5A, VcE = -2V	
Base-Emitter Turn-On Voltage (Note 10)		_	-815	-900	mV	Ic = -2.5A, VcE = -2V	
	hFE	200	350	_	_	Ic = -10mA, VcE = -2V	
		250	340	420	_	I _C = -100mA, V _{CE} = -2V	
DC Current Cain (Note 10)		220	300	_	_	Ic = -0.5A, VcE = -2V	
DC Current Gain (Note 10)		160	260	_	_	Ic = -1A, VcE = -2V	
		60	130	_	_	I _C = -1.5A, V _{CE} = -2V	
		15	35	_	_	Ic = -2.5A, VcE = -2V	
Input Capacitance	Cibo	_	300	_	pF	V _{EB} = 0.5V. f = 1MHz	
Output Capacitance	Cobo	_	21	_	pF	V _{CB} = 10V, f = 1MHz	
Current Gain-Bandwidth Product	f _T	150	290	_	MHz	V _{CE} = -10V, I _C = -100mA f = 50MHz	
Turn-On Time	td	_	13.5	_	ns		
Turn-On Time	tr	1	90		ns	Vcc = -10V, Ic = -1.5A	
Turn Off Time	ts	_	255	_	ns	$I_{B1} = -I_{B2} = -150 \text{mA}$	
Turn-Off Time	t _f		48		ns		
	idth < 2000 Dut.						

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

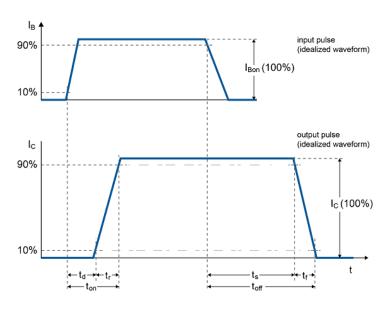
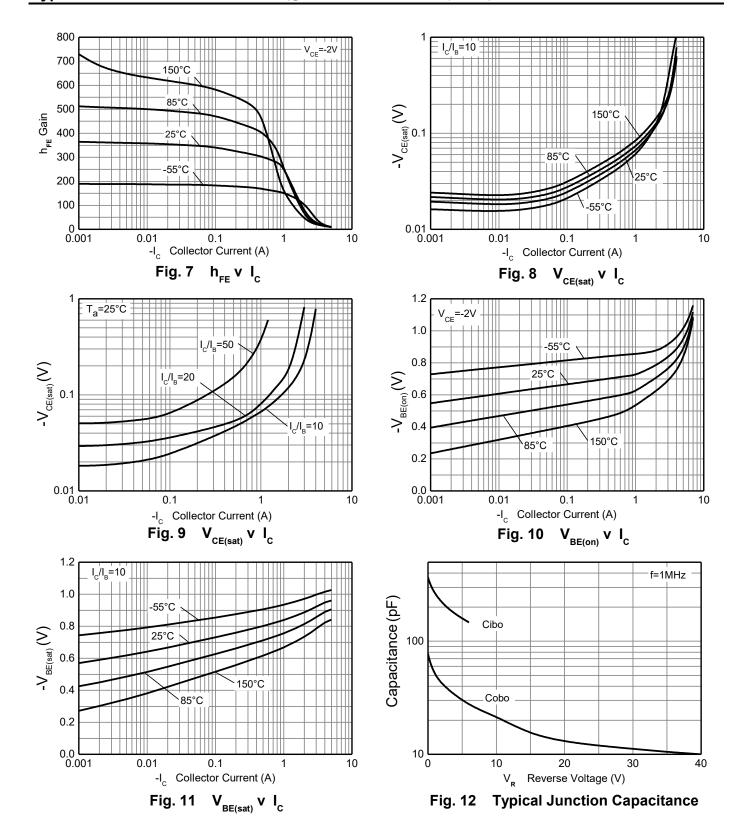


Fig 6. Timing Waveform



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Typical Electrical Characteristics (continued) (@TA = +25°C, unless otherwise specified.)

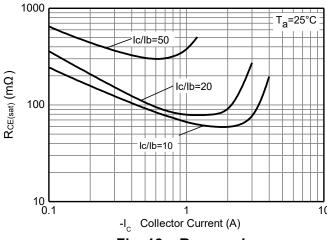


Fig. 13 $R_{CE(sat)} v I_{C}$

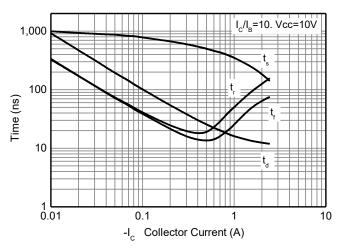


Fig. 15 Switching Performance

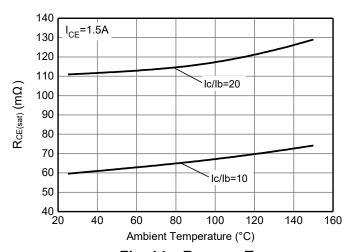


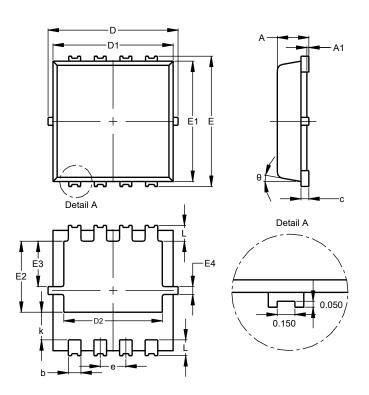
Fig. 14 R_{CE(sat)} v T_{amb}



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

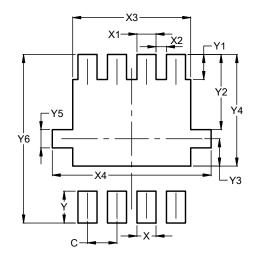


PowerDI3333-8/SWP						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Notes:

- 11. For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.12. Side wall tin plated package for wettable flanks in AOI.



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